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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 20x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100pjdfa-v0

Table 1-1. List of Ordering Part Numbers

(3/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	Mounted	A	R5F100CAALA#U0, R5F100CCALA#U0, R5F100CDALA#U0, R5F100CEALA#U0, R5F100CFALA#U0, R5F100CGALA#U0 R5F100CAALA#W0, R5F100CCALA#W0, R5F100CDALA#W0, R5F100CEALA#W0, R5F100CFALA#W0, R5F100CGALA#W0 R5F100CAGLA#U0, R5F100CCGLA#U0, R5F100CDGLA#U0, R5F100CEGLA#U0, R5F100CFGLA#U0, R5F100CGGLA#U0 R5F100CAGLA#W0, R5F100CCGLA#W0, R5F100CDGLA#W0, R5F100CEGLA#W0, R5F100CFGLA#W0, R5F100CGGLA#W0
		Not mounted	A	R5F101CAALA#U0, R5F101CCALA#U0, R5F101CDALA#U0, R5F101CEALA#U0, R5F101CFALA#U0, R5F101CGALA#U0 R5F101CAALA#W0, R5F101CCALA#W0, R5F101CDALA#W0, R5F101CEALA#W0, R5F101CFALA#W0, R5F101CGALA#W0
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	Mounted	A	R5F100EAANA#U0, R5F100ECANA#U0, R5F100EDANA#U0, R5F100EEANA#U0, R5F100EFANA#U0, R5F100EGANA#U0, R5F100EHANA#U0 R5F100EAANA#W0, R5F100ECANA#W0, R5F100EDANA#W0, R5F100EEANA#W0, R5F100EFANA#W0, R5F100EGANA#W0, R5F100EHANA#W0 R5F100EADNA#U0, R5F100ECDNA#U0, R5F100EDDNA#U0, R5F100EEDNA#U0, R5F100EFDNA#U0, R5F100EGDNA#U0, R5F100EHDNA#U0 R5F100EADNA#W0, R5F100ECDNA#W0, R5F100EDDNA#W0, R5F100EEDNA#W0, R5F100EFDNA#W0, R5F100EGDNA#W0, R5F100EHDNA#W0 R5F100EAGNA#U0, R5F100ECGNA#U0, R5F100EDGNA#U0, R5F100EEGNA#U0, R5F100EFGNA#U0, R5F100EGGNA#U0, R5F100EHGNA#U0 R5F100EAGNA#W0, R5F100ECGNA#W0, R5F100EDGNA#W0, R5F100EEGNA#W0, R5F100EFGNA#W0, R5F100EGGNA#W0, R5F100EHGNA#W0
		Not mounted	A	R5F101EAANA#U0, R5F101ECANA#U0, R5F101EDANA#U0, R5F101EEANA#U0, R5F101EFANA#U0, R5F101EGANA#U0, R5F101EHANA#U0 R5F101EAANA#W0, R5F101ECANA#W0, R5F101EDANA#W0, R5F101EEANA#W0, R5F101EFANA#W0, R5F101EGANA#W0, R5F101EHANA#W0 R5F101EADNA#U0, R5F101ECDNA#U0, R5F101EDDNA#U0, R5F101EEDNA#U0, R5F101EFDNA#U0, R5F101EGDNA#U0, R5F101EHDNA#U0 R5F101EADNA#W0, R5F101ECDNA#W0, R5F101EDDNA#W0, R5F101EEDNA#W0, R5F101EFDNA#W0, R5F101EGDNA#W0, R5F101EHDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(4/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)	Mounted	A	R5F100FAAFP#V0, R5F100FCAFP#V0, R5F100FDAFP#V0, R5F100FEAFP#V0, R5F100FFAFP#V0, R5F100FGAFP#V0, R5F100FHAFP#V0, R5F100FJAFP#V0, R5F100FKAFP#V0, R5F100FLAFP#V0 R5F100FAAFP#X0, R5F100FCAFP#X0, R5F100FDAFP#X0, R5F100FEAFP#X0, R5F100FFAFP#X0, R5F100FGAFP#X0, R5F100FHAFP#X0, R5F100FJAFP#X0, R5F100FKAFP#X0, R5F100FLAFP#X0
			D	R5F100FADFP#V0, R5F100FCDFP#V0, R5F100FDDFP#V0, R5F100FEDFP#V0, R5F100FFDFP#V0, R5F100FGDFP#V0, R5F100FHDFP#V0, R5F100FJDFP#V0, R5F100FKDFP#V0, R5F100FLDFP#V0 R5F100FADFP#X0, R5F100FCDFP#X0, R5F100FDDFP#X0, R5F100FEDFP#X0, R5F100FFDFP#X0, R5F100FGDFP#X0, R5F100FHDFP#X0, R5F100FJDFP#X0, R5F100FKDFP#X0, R5F100FLDFP#X0
			G	R5F100FAGFP#V0, R5F100FCGFP#V0, R5F100FDGFP#V0, R5F100FEGFP#V0, R5F100FFGFP#V0, R5F100FGGFP#V0, R5F100FHGFP#V0, R5F100FJGFP#V0 R5F100FAGFP#X0, R5F100FCGFP#X0, R5F100FDGFP#X0, R5F100FEGFP#X0, R5F100FFGFP#X0, R5F100FGGFP#X0, R5F100FHGFP#X0, R5F100FJGFP#X0
		Not mounted	A	R5F101FAAFP#V0, R5F101FCAFP#V0, R5F101FDAFP#V0, R5F101FEAFP#V0, R5F101FFAFP#V0, R5F101FGAFP#V0, R5F101FHAFP#V0, R5F101FJAFP#V0, R5F101FKAFP#V0, R5F101FLAFP#V0 R5F101FAAFP#X0, R5F101FCAFP#X0, R5F101FDAFP#X0, R5F101FEAFP#X0, R5F101FFAFP#X0, R5F101FGAFP#X0, R5F101FHAFP#X0, R5F101FJAFP#X0, R5F101FKAFP#X0, R5F101FLAFP#X0
			D	R5F101FADFP#V0, R5F101FCDFP#V0, R5F101FDDFP#V0, R5F101FEDFP#V0, R5F101FFDFP#V0, R5F101FGDFP#V0, R5F101FHDFP#V0, R5F101FJDFP#V0, R5F101FKDFP#V0, R5F101FLDFP#V0 R5F101FADFP#X0, R5F101FCDFP#X0, R5F101FDDFP#X0, R5F101FEDFP#X0, R5F101FFDFP#X0, R5F101FGDFP#X0, R5F101FHDFP#X0, R5F101FJDFP#X0, R5F101FKDFP#X0, R5F101FLDFP#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

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Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F100LCAFB#V0, R5F100LDAFB#V0, R5F100LEAFB#V0, R5F100LFAFB#V0, R5F100LGAFB#V0, R5F100LHAFB#V0, R5F100LJAFB#V0, R5F100LKAFB#V0, R5F100LLAFB#V0 R5F100LCAFB#X0, R5F100LDAFB#X0, R5F100LEAFB#X0, R5F100LFAFB#X0, R5F100LGAFB#X0, R5F100LHAFB#X0, R5F100LJAFB#X0, R5F100LKAFB#X0, R5F100LLAFB#X0
			D	R5F100LCDFB#V0, R5F100LDDFB#V0, R5F100LEDFB#V0, R5F100LFDDB#V0, R5F100LGDFB#V0, R5F100LHDFB#V0, R5F100LJDFB#V0, R5F100LKDFB#V0, R5F100LLDFB#V0 R5F100LCDFB#X0, R5F100LDDFB#X0, R5F100LEDFB#X0, R5F100LFDDB#X0, R5F100LGDFB#X0, R5F100LHDFB#X0, R5F100LJDFB#X0, R5F100LKDFB#X0, R5F100LLDFB#X0
			G	R5F100LCGFB#V0, R5F100LDGFB#V0, R5F100LEGFB#V0, R5F100LFGFB#V0 R5F100LCGFB#X0, R5F100LDGFB#X0, R5F100LEGFB#X0, R5F100LFGFB#X0 R5F100LGGFB#V0, R5F100LHGFB#V0, R5F100LJGFB#V0 R5F100LGGFB#X0, R5F100LHGFB#X0, R5F100LJGFB#X0
	64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)	Not mounted	A	R5F101LCAFB#V0, R5F101LDAFB#V0, R5F101LEAFB#V0, R5F101LFAFB#V0, R5F101LGAFB#V0, R5F101LHAFB#V0, R5F101LJAFB#V0, R5F101LKAFB#V0, R5F101LLAFB#V0 R5F101LCAFB#X0, R5F101LDAFB#X0, R5F101LEAFB#X0, R5F101LFAFB#X0, R5F101LGAFB#X0, R5F101LHAFB#X0, R5F101LJAFB#X0, R5F101LKAFB#X0, R5F101LLAFB#X0
			D	R5F101LCDFB#V0, R5F101LDDFB#V0, R5F101LEDFB#V0, R5F101LFDDB#V0, R5F101LGDFB#V0, R5F101LHDFB#V0, R5F101LJDFB#V0, R5F101LKDFB#V0, R5F101LLDFB#V0 R5F101LCDFB#X0, R5F101LDDFB#X0, R5F101LEDFB#X0, R5F101LFDDB#X0, R5F101LGDFB#X0, R5F101LHDFB#X0, R5F101LJDFB#X0, R5F101LKDFB#X0, R5F101LLDFB#X0
	64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)	Mounted	A	R5F100LCABG#U0, R5F100LDABG#U0, R5F100LEABG#U0, R5F100LFABG#U0, R5F100LGABG#U0, R5F100LHABG#U0, R5F100LJABG#U0 R5F100LCABG#W0, R5F100LDABG#W0, R5F100LEABG#W0, R5F100LFABG#W0, R5F100LGABG#W0, R5F100LHABG#W0, R5F100LJABG#W0
			G	R5F100LCGBG#U0, R5F100LDGBG#U0, R5F100LEGBG#U0, R5F100LFGBG#U0, R5F100LGGBG#U0, R5F100LHGBG#U0, R5F100LJGBG#U0 R5F100LCGBG#W0, R5F100LDGBG#W0, R5F100LEGBG#W0, R5F100LFGBG#W0, R5F100LGGBG#W0, R5F100LHGBG#W0, R5F100LJGBG#W0
	64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)	Not mounted	A	R5F101LCABG#U0, R5F101LDABG#U0, R5F101LEABG#U0, R5F101LFABG#U0, R5F101LGABG#U0, R5F101LHABG#U0, R5F101LJABG#U0 R5F101LCABG#W0, R5F101LDABG#W0, R5F101LEABG#W0, R5F101LFABG#W0, R5F101LGABG#W0, R5F101LHABG#W0, R5F101LJABG#W0

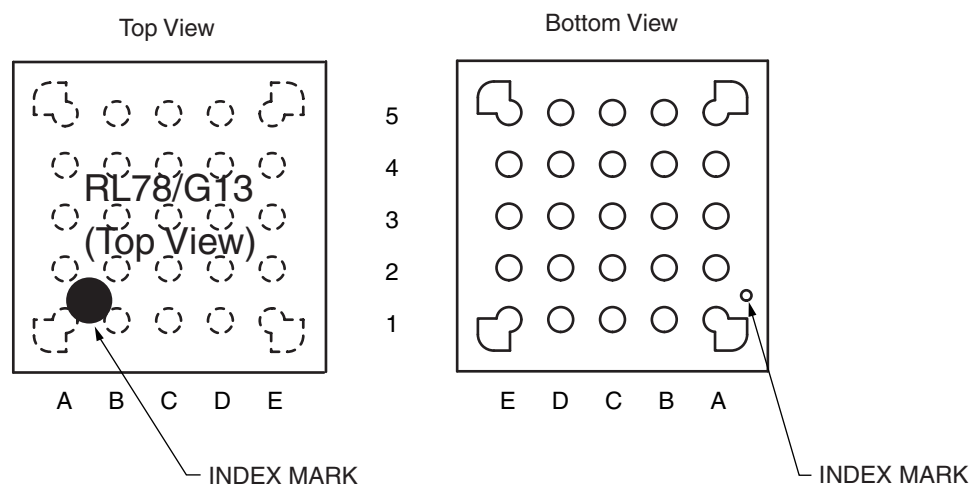
Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.3 25-pin products

- 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch)

<R>



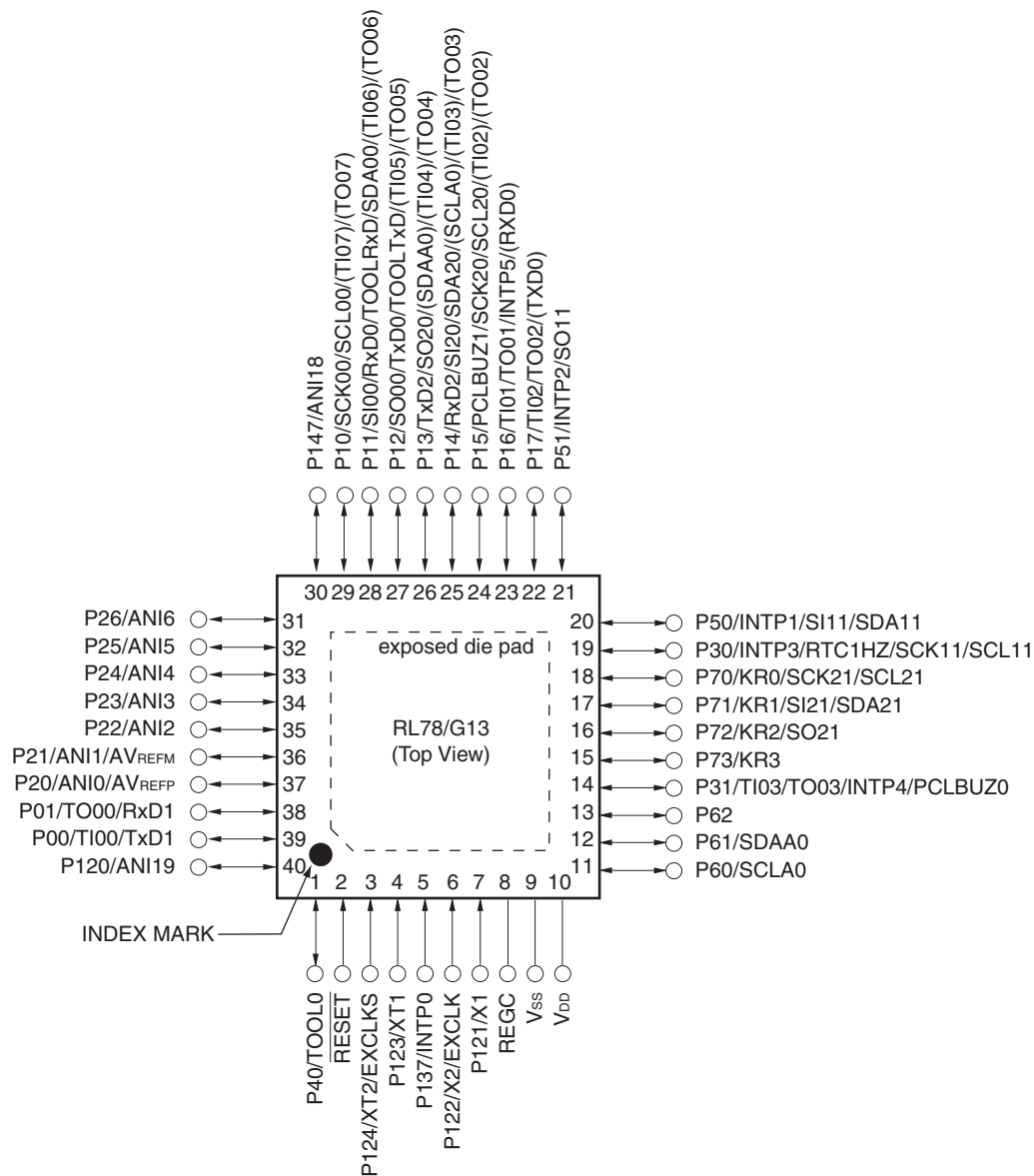
	A	B	C	D	E	
5	P40/TOOL0	RESET	P01/ANI16/ TO00/RxD1	P22/ANI2	P147/ANI18	5
4	P122/X2/ EXCLK	P137/INTP0	P00/ANI17/ TI00/TxD1	P21/ANI1/ AV _{REFM}	P10/SCK00/ SCL00	4
3	P121/X1	V _{DD}	P20/ANI0/ AV _{REFP}	P12/SO00/ TxD0/ TOOLTxD	P11/SI00/ RxD0/ TOOLRxD/ SDA00	3
2	REGC	V _{SS}	P30/INTP3/ SCK11/SCL11	P17/TI02/ TO02/SO11	P50/INTP1/ SI11/SDA11	2
1	P60/SCLA0	P61/SDAA0	P31/TI03/ TO03/INTP4/ PCLBUZ0	P16/TI01/ TO01/INTP5	P130	1
	A	B	C	D	E	

Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

Remark For pin identification, see 1.4 Pin Identification.

1.3.7 40-pin products

- 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)

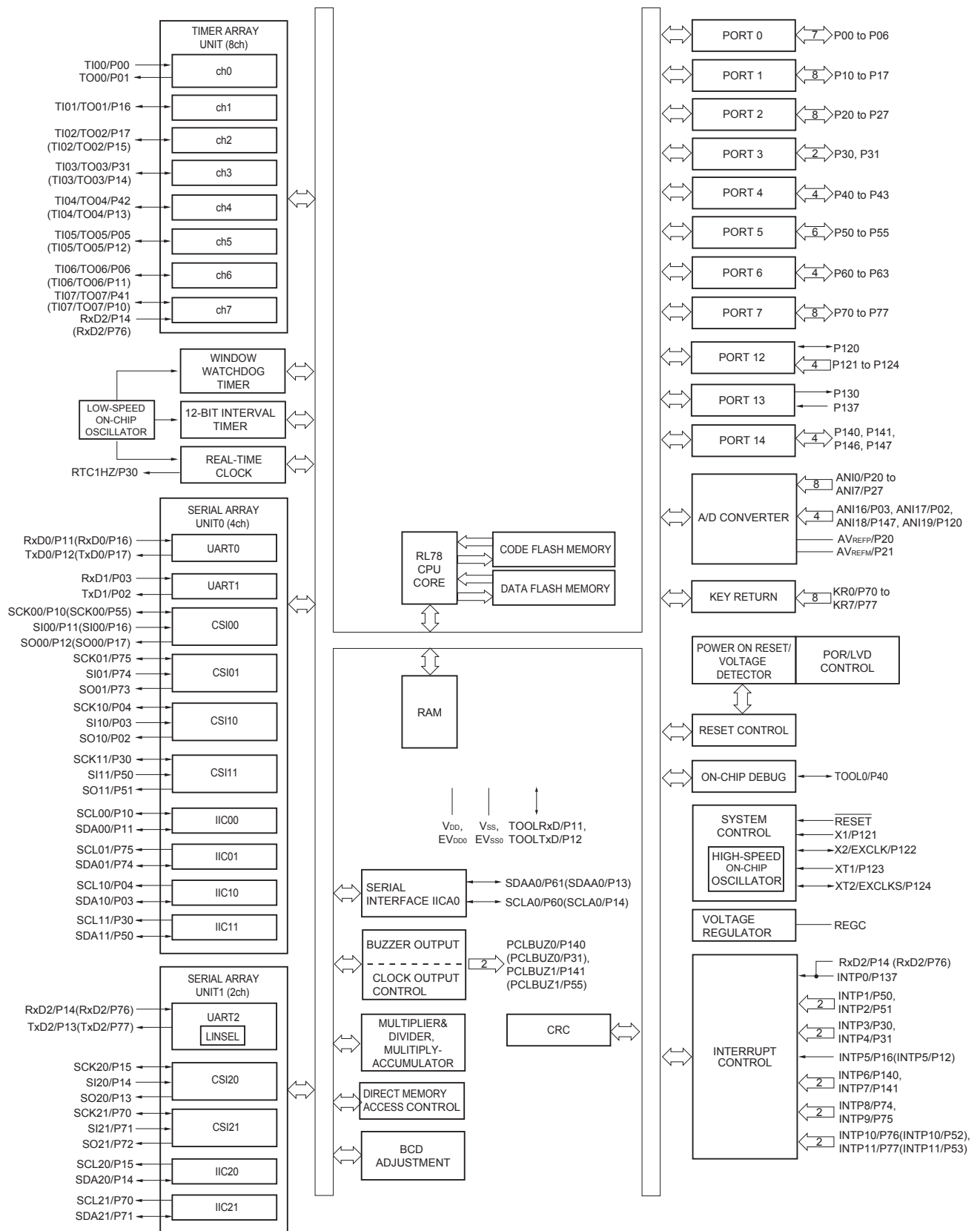


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
- It is recommended to connect an exposed die pad to Vss.

1.5.11 64-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		40-pin		44-pin		48-pin		52-pin		64-pin	
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Code flash memory (KB)		16 to 192		16 to 512		16 to 512		32 to 512		32 to 512	
Data flash memory (KB)		4 to 8	—	4 to 8	—	4 to 8	—	4 to 8	—	4 to 8	—
RAM (KB)		2 to 16 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}	
Address space		1 MB									
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)									
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)									
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz									
Low-speed on-chip oscillator		15 kHz (TYP.)									
General-purpose registers		(8-bit register × 8) × 4 banks									
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)									
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)									
		30.5 μs (Subsystem clock: f _{SUB} = 32.768 kHz operation)									
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.									
I/O port	Total	36		40		44		48		58	
	CMOS I/O	28 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)		31 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)		34 (N-ch O.D. I/O [V _{DD} withstand voltage]: 11)		38 (N-ch O.D. I/O [V _{DD} withstand voltage]: 13)		48 (N-ch O.D. I/O [V _{DD} withstand voltage]: 15)	
	CMOS input	5		5		5		5		5	
	CMOS output	—		—		1		1		1	
	N-ch O.D. I/O (withstand voltage: 6 V)	3		4		4		4		4	
Timer	16-bit timer	8 channels									
	Watchdog timer	1 channel									
	Real-time clock (RTC)	1 channel									
	12-bit interval timer (IT)	1 channel									
	Timer output	4 channels (PWM outputs: 3 ^{Note2}), 8 channels (PWM outputs: 7 ^{Note2, Note3})		5 channels (PWM outputs: 4 ^{Note2}), 8 channels (PWM outputs: 7 ^{Note2}) ^{Note3}						8 channels (PWM outputs: 7 ^{Note2})	
	RTC output	1 channel • 1 Hz (subsystem clock: f _{SUB} = 32.768 kHz)									

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory. The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EV _{SS0} , EV _{SS1}	EV _{SS0} = EV _{SS1}	-0.5 to +0.3	V
REGC pin input voltage	V _{IREGC}	REGC	-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	V _{I1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	-0.3 to EV _{DD0} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	V _{I3}	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Output voltage	V _{O1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-0.3 to EV _{DD0} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Analog input voltage	V _{AI1}	ANI16 to ANI26	-0.3 to EV _{DD0} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V
	V _{AI2}	ANI0 to ANI14	-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V

Notes 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed AV_{REF}(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. AV_{REF}(+) : + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(T_A = -40 to +85°C, 1.6 V ≤ E_{VDD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = E_{VSS0} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.54	1.63	mA	
					V _{DD} = 3.0 V		0.54	1.63	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.28	mA	
					V _{DD} = 3.0 V		0.44	1.28	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.40	1.00	mA	
					V _{DD} = 3.0 V		0.40	1.00	mA	
			LS (low-speed main) mode Note 7	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA	
					V _{DD} = 2.0 V		260	530	μA	
			LV (low-voltage main) mode Note 7	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		420	640	μA	
					V _{DD} = 2.0 V		420	640	μA	
			HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.28	1.00	mA	
					Resonator connection		0.45	1.17	mA	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.28	1.00	mA	
					Resonator connection		0.45	1.17	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.19	0.60	mA	
					Resonator connection		0.26	0.67	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.19	0.60	mA	
					Resonator connection		0.26	0.67	mA	
			LS (low-speed main) mode Note 7	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		95	330	μA	
					Resonator connection		145	380	μA	
				f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V	Square wave input		95	330	μA	
					Resonator connection		145	380	μA	
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.25	0.57	μA	
					Resonator connection		0.44	0.76	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.30	0.57	μA	
					Resonator connection		0.49	0.76	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.37	1.17	μA	
					Resonator connection		0.56	1.36	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.53	1.97	μA	
					Resonator connection		0.72	2.16	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		0.82	3.37	μA	
					Resonator connection		1.01	3.56	μA	
	I _{DD3} Note 6	STOP mode Note 8	T _A = −40°C					0.18	0.50	μA
			T _A = +25°C					0.23	0.50	μA
			T _A = +50°C					0.30	1.10	μA
			T _A = +70°C					0.46	1.90	μA
			T _A = +85°C					0.75	3.30	μA

(Notes and Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V		Note 1		Note 1		Note 1	bps
					2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		Note 3		Note 3		Note 3	bps
					1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
					0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Notes 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

2. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	t _{KH2} , t _{KL2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	t _{KCY2} /2 - 12		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	t _{KCY2} /2 - 18		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
Slp setup time (to SCKp↑) ^{Note 3}	t _{SIK2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	1/f _{MCK} + 30		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
Slp hold time (from SCKp↑) ^{Note 4}	t _{KS12}		1/f _{MCK} + 31		1/f _{MCK} + 31		1/f _{MCK} + 31		ns
Delay time from SCKp↓ to SOp output ^{Note 5}	t _{KSO2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		2/f _{MCK} + 120		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		2/f _{MCK} + 214		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ		2/f _{MCK} + 573		2/f _{MCK} + 573		2/f _{MCK} + 573	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps2. Use it with EV_{DD0} ≥ V_b.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

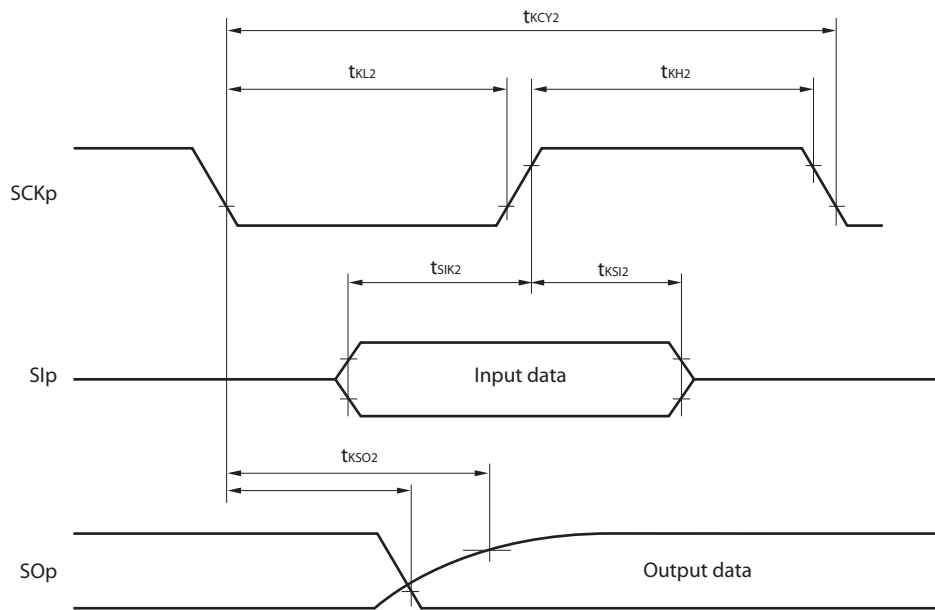
4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

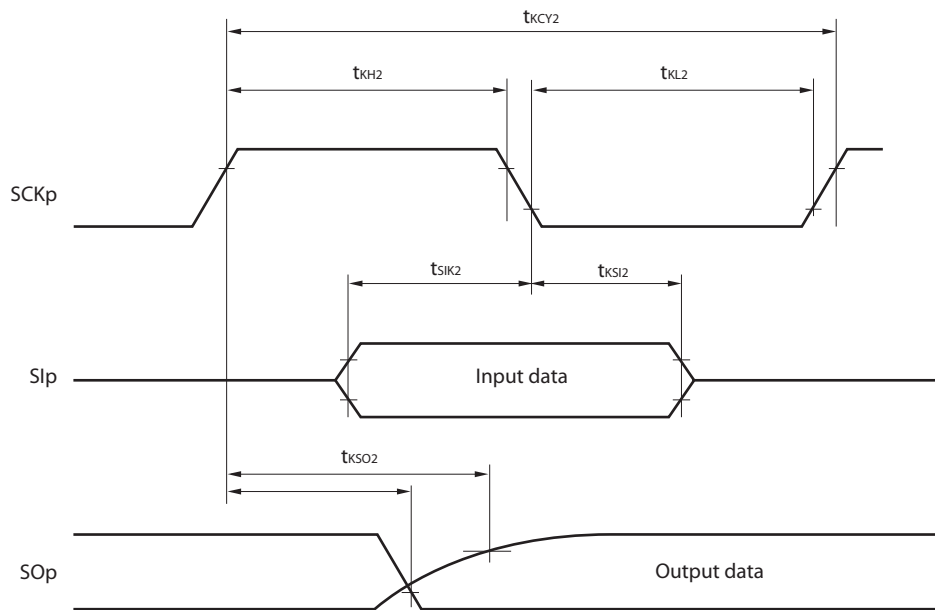
Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks**
1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,
n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

2.5.2 Serial interface IICA

(1) I²C standard mode(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Standard mode: f _{CLK} ≥ 1 MHz	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		0	100	0	100	kHz
Setup time of restart condition	t _{SU:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		4.7		4.7		μs	
Hold time ^{Note 1}	t _{HD:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		4.0		4.0		μs	
Hold time when SCLA0 = “L”	t _{LOW}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		4.7		4.7		μs	
Hold time when SCLA0 = “H”	t _{HIGH}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		4.0		4.0		μs	
Data setup time (reception)	t _{SU:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	250		250		250		ns	
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	250		250		250		ns	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	250		250		250		ns	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		250		250		ns	
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs	
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		0	3.45	0	3.45	μs	
Setup time of stop condition	t _{SU:STO}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	4.0		4.0		4.0		μs	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		4.0		4.0		μs	
Bus-free time	t _{BUF}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	4.7		4.7		4.7		μs	
		1.6 V ≤ EV _{DD0} ≤ 5.5 V	—		4.7		4.7		μs	

(Notes, Caution and Remark are listed on the next page.)

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±2.5	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14	0			V _{DD}	V
		ANI16 to ANI26	0			EV _{DD0}	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{BGR} ^{Note 4}				V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{TMPS25} ^{Note 4}				V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_x) ^{Note}	Ceramic resonator/ crystal resonator	$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	1.0		20.0	MHz
		$2.4\text{ V} \leq V_{DD} < 2.7\text{ V}$	1.0		16.0	MHz
XT1 clock oscillation frequency (f_x) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator.

3.2.2 On-chip oscillator characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	f_{IH}			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to $+85^\circ\text{C}$	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-1.0		$+1.0$	%
		-40 to -20°C	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-1.5		$+1.5$	%
		$+85$ to $+105^\circ\text{C}$	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-2.0		$+2.0$	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		$+15$	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

- Notes**
1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

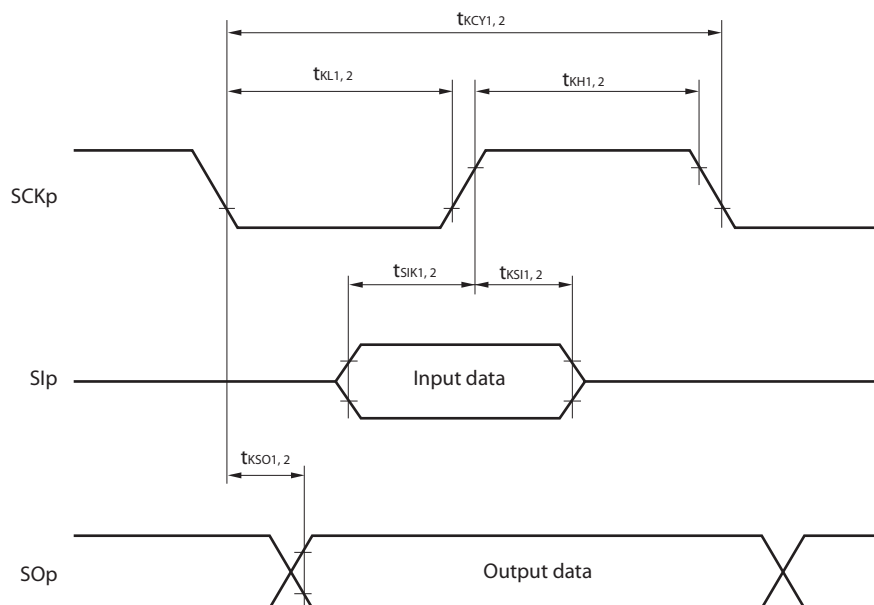
(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$) (2/2)

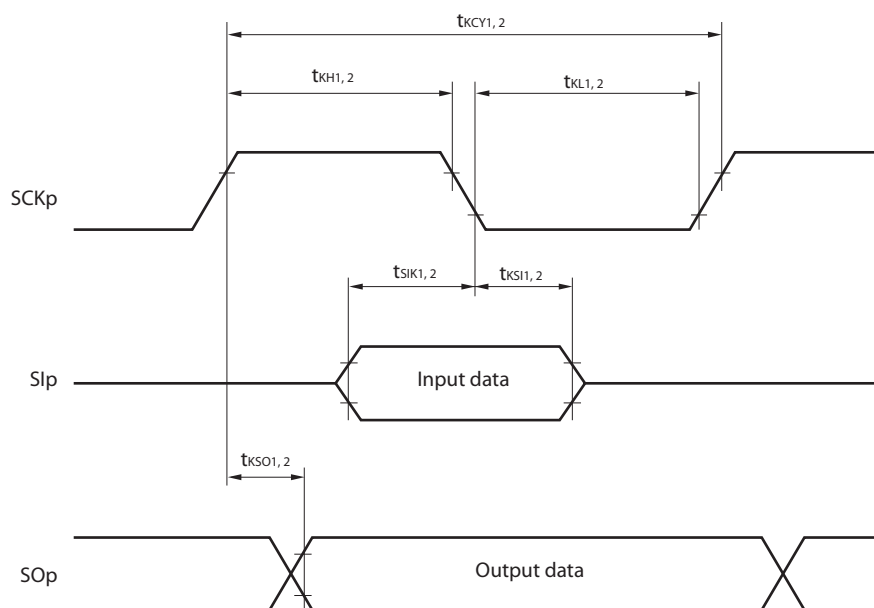
Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.62	3.40	mA	
					V _{DD} = 3.0 V		0.62	3.40	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	2.70	mA	
					V _{DD} = 3.0 V		0.50	2.70	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.90	mA	
					V _{DD} = 3.0 V		0.44	1.90	mA	
				HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.31	2.10	mA
						Resonator connection		0.48	2.20	mA
					f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.31	2.10	mA
						Resonator connection		0.48	2.20	mA
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V		Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V		Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.28	0.61	μA	
					Resonator connection		0.47	0.80	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.34	0.61	μA	
					Resonator connection		0.53	0.80	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	2.30	μA	
					Resonator connection		0.60	2.49	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.64	4.03	μA	
					Resonator connection		0.83	4.22	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.09	8.04	μA	
					Resonator connection		1.28	8.23	μA	
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +105°C	Square wave input		5.50	41.00	μA		
				Resonator connection		5.50	41.00	μA		
	I _{DD3} ^{Note 6}	STOP mode ^{Note 8}	T _A = −40°C					0.19	0.52	μA
			T _A = +25°C					0.25	0.52	μA
			T _A = +50°C					0.32	2.21	μA
			T _A = +70°C					0.55	3.94	μA
			T _A = +85°C					1.00	7.95	μA
			T _A = +105°C					5.00	40.00	μA

(Notes and Remarks are listed on the next page.)

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Data setup time (reception)	$t_{\text{SU:DAT}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 340$ Note 2		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 340$ Note 2		ns
		$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	$1/f_{\text{MCK}} + 760$ Note 2		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 760$ Note 2		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$1/f_{\text{MCK}} + 570$ Note 2		ns
Data hold time (transmission)	$t_{\text{HD:DAT}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	0	1420	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	1420	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	0	1215	ns

Notes 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.2. Set the f_{MCK} value to keep the hold time of $\text{SCLr} = \text{"L"}$ and $\text{SCLr} = \text{"H"}$.

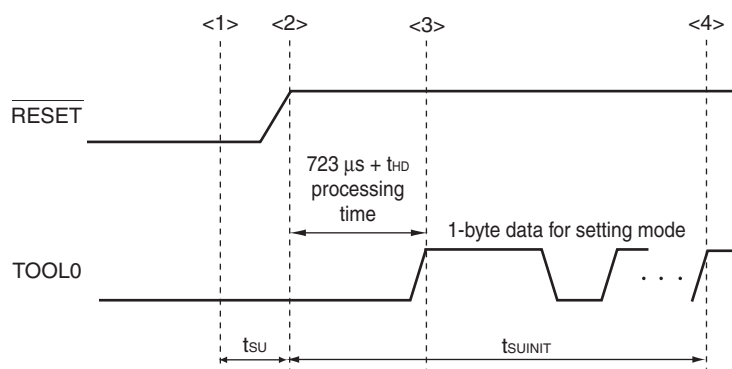
Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

3.10 Timing of Entry to Flash Memory Programming Modes

(T_A = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUNIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUNIT} : Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD} : Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)